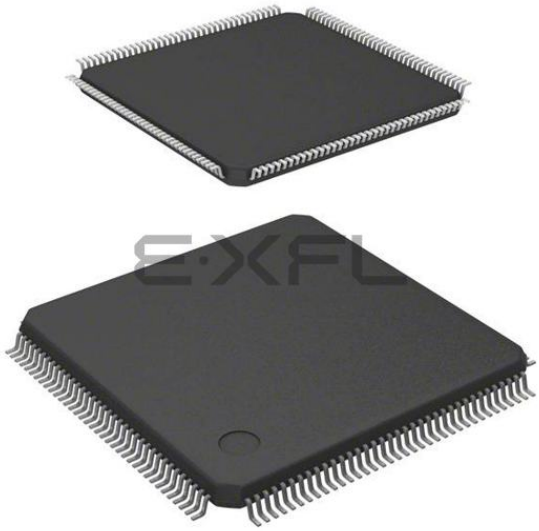


Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	ARM7®
Core Size	32-Bit Single-Core
Speed	36MHz
Connectivity	I²C, SPI, UART/USART
Peripherals	DMA, POR, PWM, WDT
Number of I/O	112
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	4.5V ~ 5.5V
Data Converters	A/D 16x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LQFP
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/str735fz1t7

Contents

Flexible clock control

Two clock sources are used to drive the microcontroller, a main clock driven by an external crystal or ceramic resonator and an internal backup RC oscillator that operates at 2 MHz or 32 kHz. The embedded PLL can be configured to generate an internal system clock of up to 36 MHz. The PLL output frequency can be programmed using a wide selection of multipliers and dividers.

Voltage regulators

The STR73xF requires an external 4.5 to 5.5 V power supply. There are two internal Voltage Regulators for generating the 1.8 V power supply needed by the core and peripherals. The main VR is switched off and the Low Power VR switched on when the application puts the STR73xF in Low Power Wait for Interrupt (LPWFI) mode.

Low voltage detectors

The voltage regulator and Flash modules each have an embedded LVD that monitors the internal 1.8 V supply. If the voltage drops below a certain threshold, the LVD will reset the STR73xF.

Note: An external power-on reset must be provided ensure the microcontroller starts-up correctly.

2.1 On-chip peripherals

CAN interfaces

The three CAN modules are compliant with the CAN specification V2.0 part B (active). The bit rate can be programmed up to 1 MBaud. These are not available in the STR735 and STR736.

DMA

4 DMA controllers, each with 4 data streams manage memory to memory, peripheral to peripheral, peripheral to memory and memory to peripheral transfers. The DMA requests are connected to TIM timers, BSPI0, BSPI1, BSPI2 and ADC. One of the streams can be configured to be triggered by a software request, independently from any peripheral activity.

16-bit timers (TIM)

Each of the ten timers (six in 100-pin devices) have a 16-bit free-running counter with 7-bit prescaler, up to two input capture/output compare functions, a pulse counter function, and a PWM channel with selectable frequency. This provides a total of 16 independent PWMs (12 in 100-pin devices) when added with the PWM modules (see next paragraph).

PWM modules (PWM)

The six 16-bit PWM modules have independently programmable periods and duty-cycles, with 5+3 bit prescaler factor.

Timebase timers (TB)

The three 16-bit timebase timers with 8-bit prescaler for general purpose time triggering operations.

Real-time clock (RTC)

The RTC provides a set of continuously running counters driven by separate clock signal derived from the main oscillator. The RTC can be used as a general timebase or

3 Block diagram

Figure 1. STR730F/STR735F block diagram

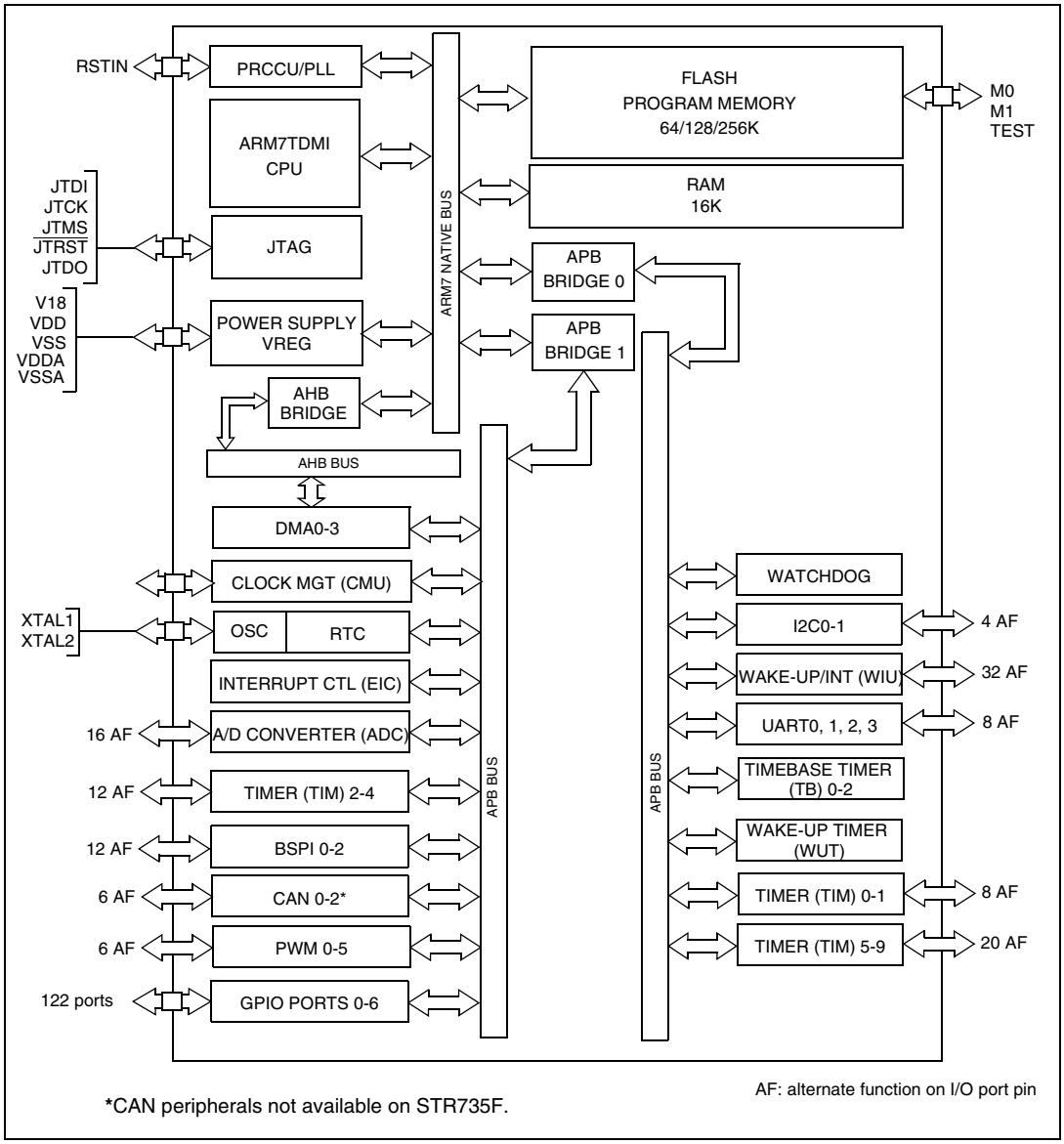
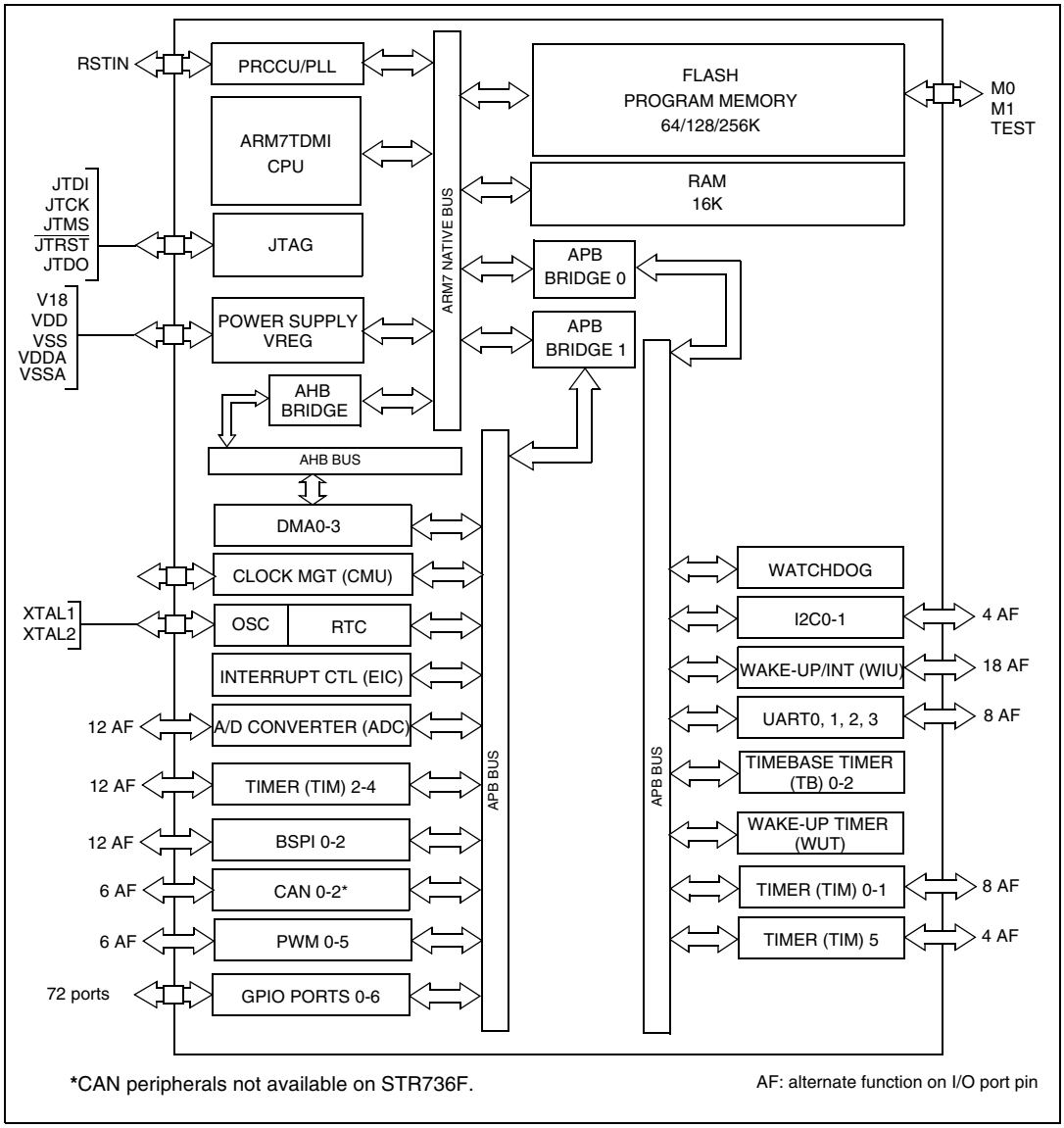


Figure 2. STR731F/STR736 block diagram



*CAN peripherals not available on STR736F.

AF: alternate function on I/O port pin

3.1 Related documentation

Available from www.arm.com:

ARM7TDMI technical reference manual

Available from http://www.st.com:

STR73x reference manual (RM0001)

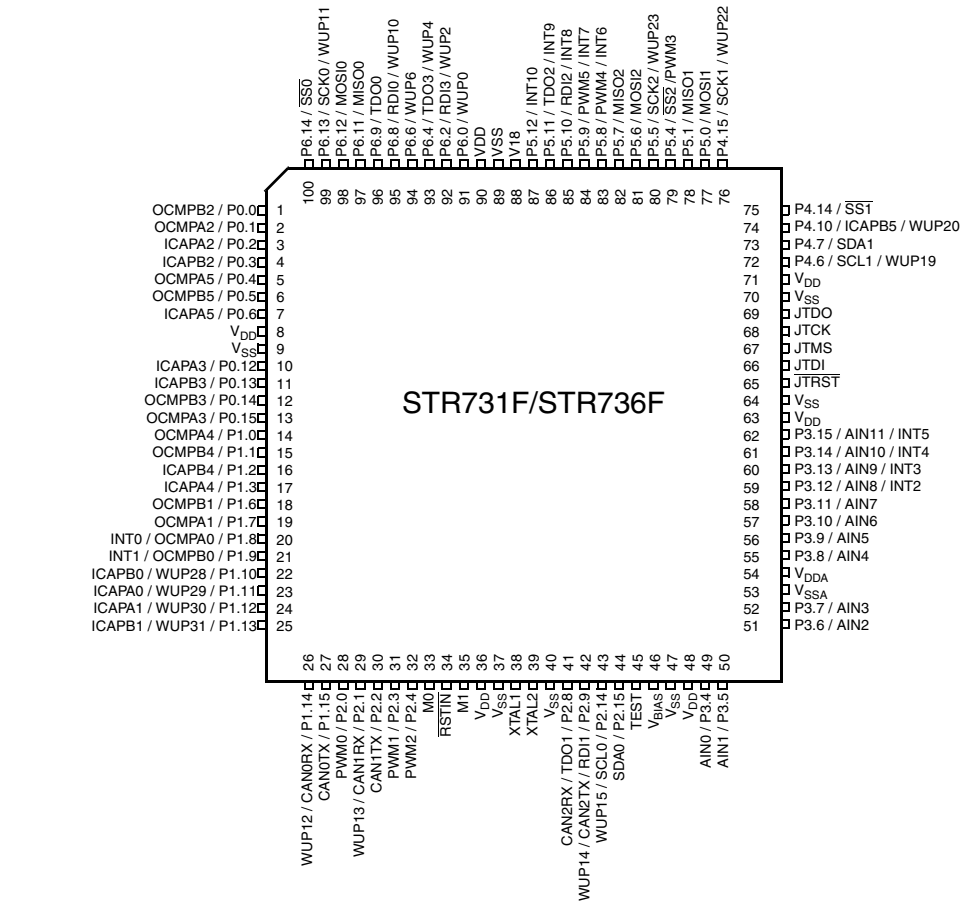
STR7 Flash programming reference manual

STR73x software library user manual

For a list of related application notes refer to http://www.st.com.

3.2.3 STR731F/STR736F (TQFP100)

Figure 4. STR731F/STR736F pin configuration (top view)



Note: CAN alternate functions not available on STR736F.

Table 4. STR73xF pin description

Pin n°			Pin name	Type	Input			Output			Main function (after reset)	Alternate function	
TQFP144	LFBGA144	TQFP100			Input Level	pu/pd	interrupt	Capability	OD	PP			
97	F9		P4.3/ICAPB8	I/O	T_T		WUP27	2mA	X	X	Port 4.3	TIM8: input capture B input	
98	F8		P4.4/CAN2TX	I/O	T_T			2mA	X	X	Port 4.4	CAN2: transmit data output	
99	E12		P4.5/CAN2RX	I/O	T_T		WUP18	2mA	X	X	Port 4.5	CAN2: receive data input	
100	E11	72	P4.6/SCL1	I/O	T_T		WUP19	2mA	X	X	Port 4.6	I2C1: serial clock	
101	C12	73	P4.7/SDA1	I/O	T_T			2mA	X	X	Port 4.7	I2C1: serial data	
102	B12		P4.8/OCMPA8	I/O	T_T			2mA	X	X	Port 4.8	TIM8: output compare A output	
103	E10		P4.9/ICAPB6	I/O	T_T			2mA	X	X	Port 4.9	TIM6: input capture B input	
104	E9	74	P4.10/ICAPA6/ICAPB5	I/O	T_T		WUP20	2mA	X	X	Port 4.10	TIM6: input capture A input (144-pin pkg only)	TIM5: input capture B input (TQFP100 only)
105	D12		P4.11/OCMPB8	I/O	T_T			2mA	X	X	Port 4.11	TIM8: output compare B output	
106	D11		P4.12/ICAPA9	I/O	T_T		WUP21	2mA	X	X	Port 4.12	TIM9: input capture A input	
107	D10		P4.13/ICAPB9	I/O	T_T			2mA	X	X	Port 4.13	TIM9: input capture B input	
108	C11	75	P4.14/$\overline{SS}$1	I/O	T_T			2mA	X	X	Port 4.14	BSPI1: slave select	
109	B11	76	P4.15/SCK1	I/O	T_T		WUP22	2mA	X	X	Port 4.15	BSPI1: serial clock	
110	B10	77	P5.0/MOSI1	I/O	T_T			2mA	X	X	Port 5.0	BSPI1: master output/slave input	
111	C10	78	P5.1/MISO1	I/O	T_T			2mA	X	X	Port 5.1	BSPI1: master input/Slave output	
112	A9		P5.2/OCMPA9	I/O	T_T			2mA	X	X	Port 5.2	TIM9: output compare A output	
113	B9		P5.3/OCMPB9	I/O	T_T			2mA	X	X	Port 5.3	TIM9: output compare B output	
114	C9	79	P5.4/$\overline{SS}$2/PWM3	I/O	T_T			2mA	X	X	Port 5.4	BSPI2: slave select	PWM3: PWM output (TQFP100 only)
115	D9	80	P5.5/SCK2	I/O	T_T		WUP23	2mA	X	X	Port 5.5	BSPI2: serial clock	
116	A11	81	P5.6/MOSI2	I/O	T_T			2mA	X	X	Port 5.6	BSPI2: master output/slave input	
117	A10	82	P5.7/MISO2	I/O	T_T			2mA	X	X	Port 5.7	BSPI2: master input/slave output	
118	A8	83	P5.8/PWM4	I/O	T_T		INT6	2mA	X	X	Port 5.8	PWM4: PWM output (TQFP100 only)	

4 Electrical parameters

4.1 Parameter conditions

Unless otherwise specified, all voltages are referred to V_{SS}.

4.1.1 Minimum and maximum values

Unless otherwise specified the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at T_A=25° C and T_A=T_{Amax} (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean±3Σ).

4.1.2 Typical values

Unless otherwise specified, typical data are based on T_A=25° C and V_{DD}=5 V. They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated (mean±2Σ).

4.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

4.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in *Figure 6*.

4.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in *Figure 7*.

Figure 6. Pin loading conditions

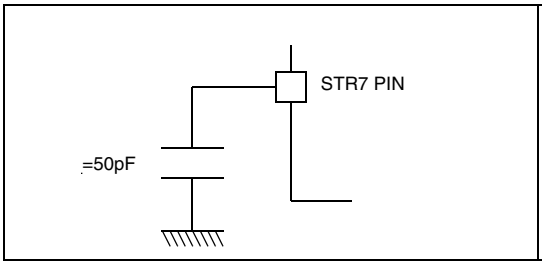
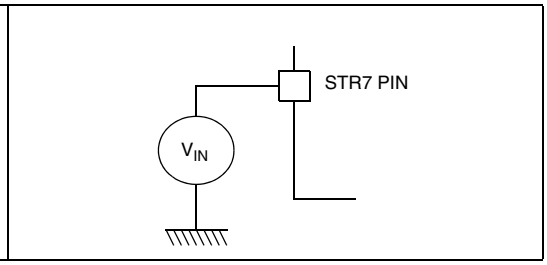


Figure 7. Pin input voltage



4.2 Absolute maximum ratings

Stresses above those listed as “absolute maximum ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device under these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Table 5. Voltage characteristics

Symbol	Ratings	Min	Max	Unit
V_{DD} - V_{SS}	External 5 V Supply voltage	-0.3	6.0	V
V_{SSA}	Reference ground for A/D converter	V_{SS}	V_{SS}	V
V_{DDA}- V_{SSA}	Reference voltage for A/D converter	-0.3	V_{DD}+0.3	V
V_{IN}	Input voltage on any pin	-0.3	V_{DD}+0.3	
$\lvert\Delta V_{DDx}\rvert$	Variations between different 5 V power pins	-	0.3	mV
$\lvert V_{SSX}$ - $V_{SS}\rvert$	Variations between all the different ground pins	-	0.3	
$V_{ESD(HBM)}$	Electrostatic discharge voltage (Human Body Model)	see *: Absolute maximum ratings (electrical sensitivity) on page 36*		
$V_{ESD(MM)}$	Electrostatic discharge voltage (Machine Model)			

Table 6. Current characteristics

Symbol	Ratings	Max.	Unit
I_{VDD}	Total current into V_{DD} power lines (source) 1)	100	mA
I_{VSS}	Total current out of V_{SS} ground lines (sink) 1)	100	
I_{IO}	Output current sunk by any I/O and control pin	10	
	Output current source by any I/O and control pin	10	
$I_{INJ(PIN)}$ 2) & 3)	Injected current on any other pin 4) &5)	±10	
$\Sigma I_{INJ(PIN)}$ 2)	Total injected current (sum of all I/O and control pins) 4)	±75	

1. All 5 V power (V_{DD}, V_{DDA}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external 5 V supply
2. $I_{INJ(PIN)}$ must never be exceeded. This is implicitly insured if V_{IN} maximum is respected. If V_{IN} maximum cannot be respected, the injection current must be limited externally to the $I_{INJ(PIN)}$ value. A positive injection is induced by $V_{IN}>V_{DD}$ while a negative injection is induced by $V_{IN}<V_{SS}$.
3. Negative injection disturbs the analog performance of the device. See note in *Section 4.3.6: 10-bit ADC characteristics on page 43*.
4. When several inputs are submitted to a current injection, the maximum $\Sigma I_{INJ(PIN)}$ is the absolute sum of the positive and negative injected currents (instantaneous values). These results are based on characterization with $\Sigma I_{INJ(PIN)}$ maximum current injection on four I/O port pins of the device.

5.) In 144-pin devices, only +10 mA on P0.3, P1.13, P3.6 and P4.13 pins (negative injection not allowed).

Table 7. Thermal characteristics

Symbol	Ratings	Value	Unit
T_{STG}	Storage temperature range	-55 to +150	°C
T_J	Maximum junction temperature (see *Section 5.2: Thermal characteristics on page 48*)		

Figure 8. STOP I_{DD} vs. VDD

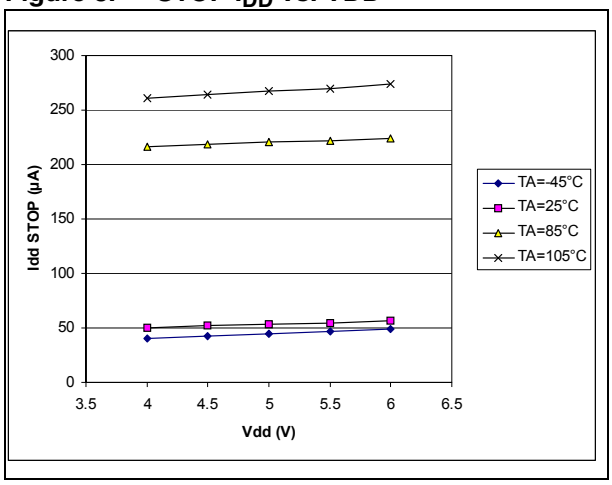


Figure 9. HALT I_{DD} vs. V_{DD}

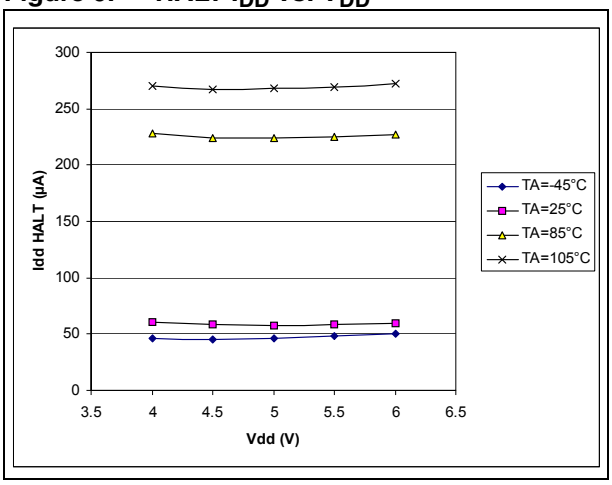


Figure 10. WFI I_{DD} vs. V_{DD}

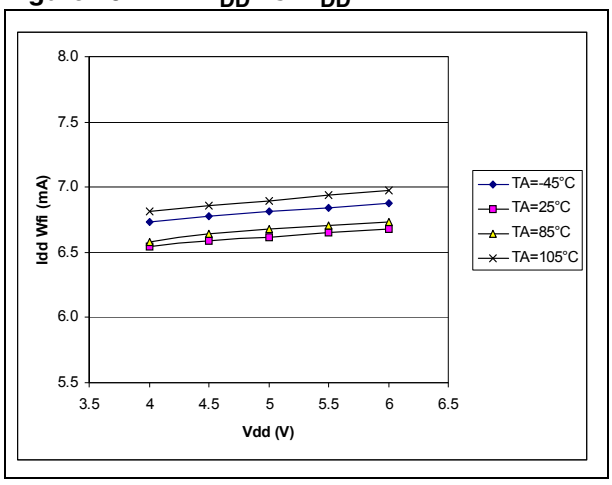
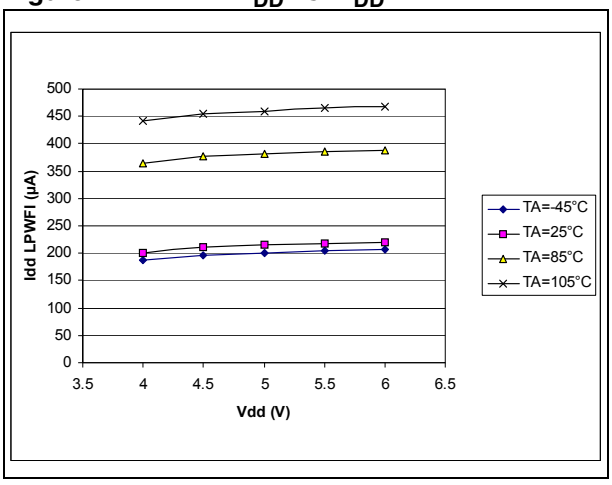


Figure 11. LPWFI I_{DD} vs. V_{DD}



4.3.3 Memory characteristics

Flash memory

Table 18. Flash memory characteristics

Symbol	Parameter	Test Conditions	Value			Unit
			Min	Typ	Max[1)]	
t_{WP}	Word program (32-bit)			35	80	µs
t_{DWP}	Double word program(64-bit)			64	150	µs
t_{BP64}	Bank program (64 K)	Double word program		0.5	1.25	s
t_{BP128}	Bank program (128 K)	Double word program		1	2.5	s
t_{BP256}	Bank program (256 K)	Double word program		2	4.9	s
t_{SE8}	Sector erase (8 K)	Not preprogrammed Preprogrammed [2)]		0.6 0.5	0.9 0.8	s
t_{SE32}	Sector erase (32 K)	Not preprogrammed Preprogrammed[2)]		1.1 0.8	2 1.8	s
t_{SE64}	Sector erase (64 K)	Not preprogrammed preprogrammed [2)]		1.7 1.3	3.7 3.3	s
t_{RPD}[3)]	Recovery from power-down				20	µs
t_{PSL}[3)]	Program suspend latency				10	µs
t_{ESL}[3)]	Erase suspend latency				30	µs
t_{ESR}[3)]	Erase suspend rate	Min. time from erase resume to next erase suspend		20	20	ms
t_{SP}[3)]	Set protection			40	170	µs
t_{FPW}[3)]	First word program			1		ms
N_{END}	Endurance		10			kcycles
t_{RET}	Data retention	T_A = 85° C	20			Years

1. T_A = -45° C after 0 cycles, Guaranteed by characterization, not tested in production.
2. All bits programmed to 0.
3. Guaranteed by design, not tested in production.

4.3.4 EMC characteristics

Susceptibility tests are performed on a sample basis during product characterization.

Functional EMS (electromagnetic susceptibility)

Based on a simple running application on the product (toggling 2 LEDs through I/O ports), the product is stressed by two electromagnetic events until a failure occurs (indicated by the LEDs).

- **ESD**: Electrostatic discharge (positive and negative) is applied on all pins of the device until a functional disturbance occurs. This test conforms with the IEC 1000-4-2 standard.
- **FTB**: A burst of fast transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test conforms with the IEC 1000-4-4 standard.

A device reset allows normal operations to be resumed. The test results are given in the table below based on the EMS levels and classes defined in application note AN1709.

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations:

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical data corruption (control registers...)

Prequalification trials:

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the RESET pin or the oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Table 19. EMS data

Symbol	Parameter	Conditions	Level/ Class
V_{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	V_{DD}=5 V, T_A=+25° C, f_{MCLK}=36 MHz conforms to IEC 1000-4-2	4A
V_{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} pins to induce a functional disturbance	V_{DD}=5 V, T_A=+25° C, f_{MCLK}=36 MHz conforms to IEC 1000-4-4	4A

Electromagnetic interference (EMI)

Based on a simple application running on the product (toggling 2 LEDs through the I/O ports), the product is monitored in terms of emission. This emission test is in line with the norm SAE J 1752/3 which specifies the board and the loading of each pin.

Table 20. EMI data

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. [f_{OSC4M}/f_{MCLK}]		Unit
				6/36 MHz	8/8 MHz	
S_{EMI}	Peak level	V_{DD}=5.0V, T_A=+25°C, All packages	0.1 MHz to 30 MHz	23	30	dBµV
			30 MHz to 130 MHz	37	34	
			130 MHz to 1 GHz	20	7	
			SAE EMI Level	4	3.5	-

Absolute maximum ratings (electrical sensitivity)

Based on three different tests (ESD, LU and DLU) using specific measurement methods, the product is stressed in order to determine its performance in terms of electrical sensitivity. For more details, refer to the application note AN1181.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts*(n+1) supply pin). Two models can be simulated: human body model and machine model. This test conforms to the JESD22-A114A/A115A standard.

Table 21. ESD Absolute Maximum ratings

Symbol	Ratings	Conditions	Maximum value [1]	Unit
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	T_A=+25° C	2000	V
$V_{ESD(MM)}$	Electrostatic discharge voltage (machine model)		200	
$V_{ESD(CDM)}$	Electrostatic discharge voltage (charge device model)		750 on corner pins, 500 on others	

Notes:

1. Data based on characterization results, not tested in production.

Static and dynamic latch-up

- **LU**: 3 complementary static tests are required on 10 parts to assess the latch-up performance. A supply overvoltage (applied to each power supply pin) and a current injection (applied to each input, output and configurable I/O pin) are performed on each

Output driving current

Subject to general operating conditions for V_{DD} and T_A unless otherwise specified.

Table 24. Output driving current

I/O Type	Symbol	Parameter	Conditions	Min	Max	Unit
Standard	V_{OL} 1)	Output low level voltage for an I/O pin when 8 pins are sunk at same time	I_{IO}=+2 mA		0.4	V
	V_{OH} 2)	Output high level voltage for an I/O pin when 4 pins are sourced at same time	I_{IO}=-2 mA	V_{DD}-0.8		
Med. Current (JTDO)	V_{OL} 1)	Output low level voltage for an I/O pin	I_{IO}=+6 mA		0.4	
	V_{OH} 2)	Output high level voltage for an I/O pin	I_{IO}=-6 mA	V_{DD}-0.8		
High Current P6.0	V_{OL} 1)	Output low level voltage for an I/O pin	I_{IO}=+8 mA		0.4	
	V_{OH} 2)	Output high level voltage for an I/O pin	I_{IO}=-8 mA	V_{DD}-0.8		

1. The I_{IO} current sunk must always respect the absolute maximum rating specified in *Table 6* and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VSS}.
2. The I_{IO} current sourced must always respect the absolute maximum rating specified in *Table 6* and the sum of I_{IO} (I/O ports and control pins) must not exceed IV_{DD}.

Figure 13. V_{OH} standard ports vs I_{OH} @ V_{DD} 5V T_A -45° C

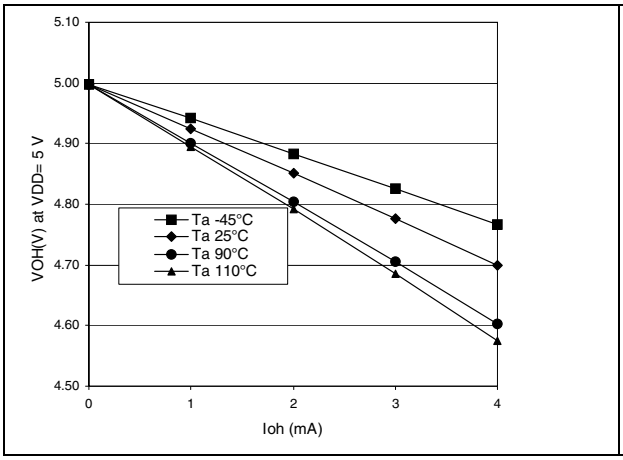


Figure 14. V_{OL} standard ports vs I_{OL} @ V_{DD} 5 V

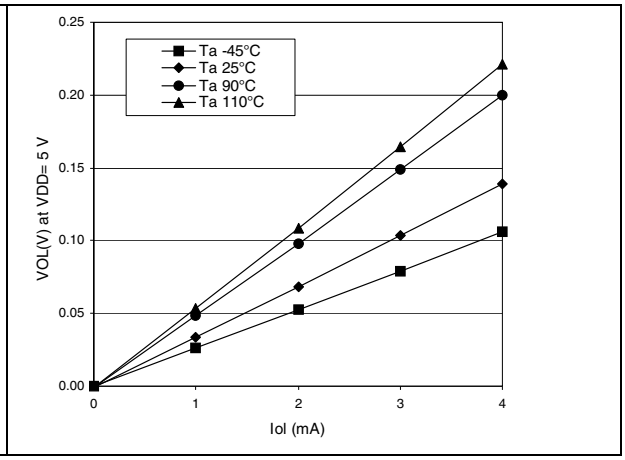


Figure 15. V_{OH} JTDO pin vs I_{OL} @ V_{DD} 5 V

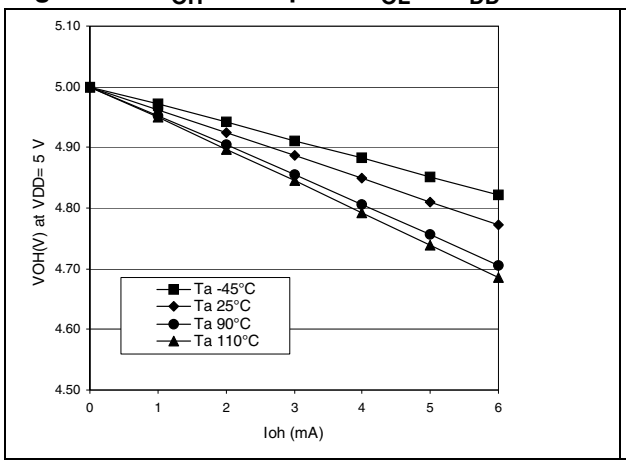


Figure 16. V_{OL} JTDO pin vs I_{OL} @ V_{DD} 5 V

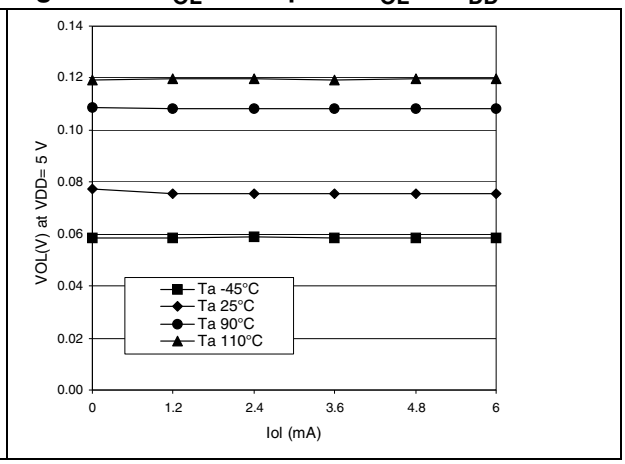


Figure 17. V_{OH} P6.0 pin vs I_{OL} @ V_{DD} 5 V

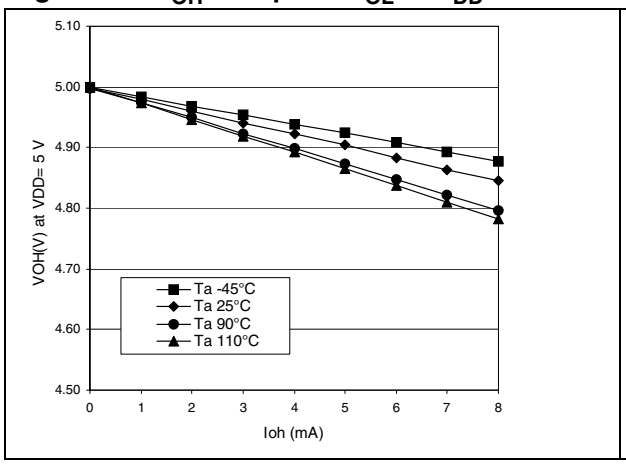
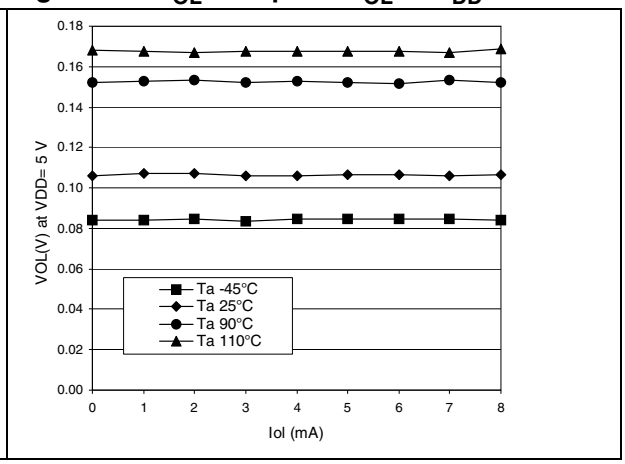


Figure 18. V_{OL} P6.0 pin vs I_{OL} @ V_{DD} 5 V



NRSTIN pin

The NRSTIN pin input driver is CMOS. A permanent pull-up is present which is the same as R_{PU} (see *: General characteristics on page 38*)

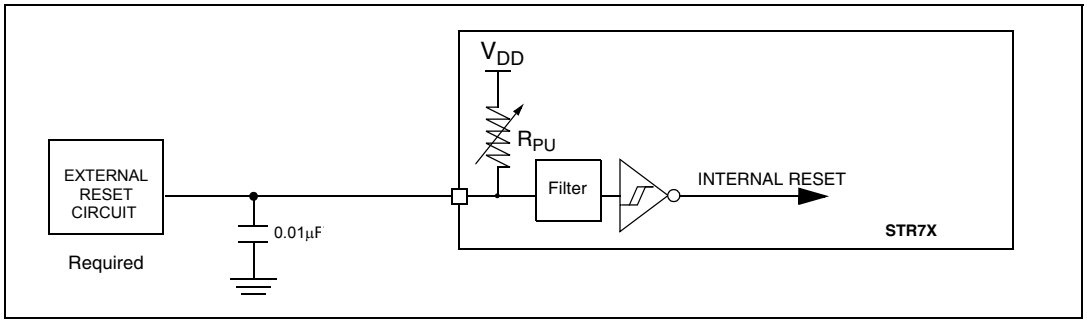
Subject to general operating conditions for V_{DD} and T_A unless otherwise specified.

Table 25. Reset pin characteristics

Symbol	Parameter	Conditions	Min	Typ [1]	Max	Unit
$V_{IL(NRSTIN)}$	NRSTIN Input low level voltage [1]				0.3 V_{DD}	V
$V_{IH(NRSTIN)}$	NRSTIN Input high level voltage [1]		0.7 V_{DD}			
$V_{hys(NRSTIN)}$	NRSTIN Schmitt trigger voltage hysteresis [2]			800		mV
$V_{F(RSTINn)}$	NRSTIN Input filtered pulse[3]				500	ns
$V_{NF(RSTINn)}$	NRSTIN Input not filtered pulse[3]		2			µs
$V_{RP(RSTINn)}$	NRSTIN removal after Power-up[3]		100			µs

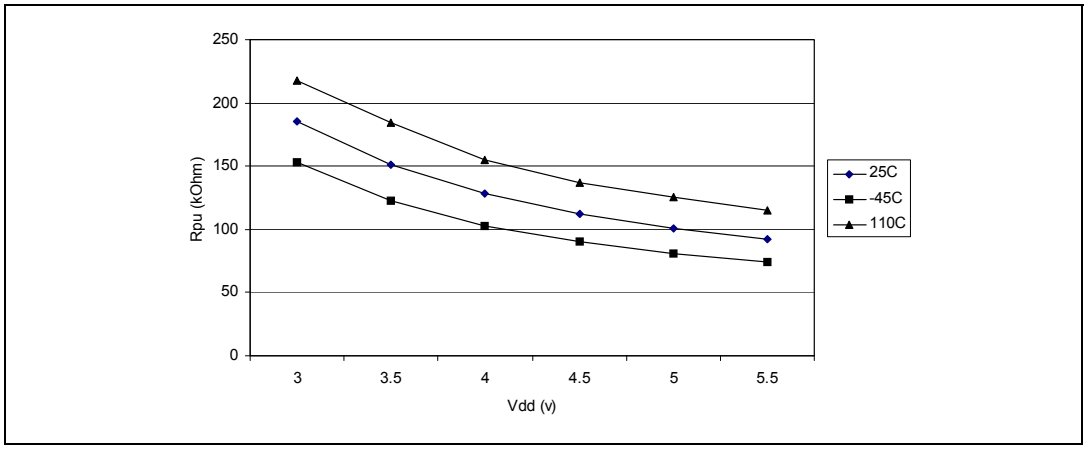
1. Data based on characterization results, not tested in production.
2. Hysteresis voltage between Schmitt trigger switching levels.
3. Data guaranteed by design, not tested in production.

Figure 19. Recommended NRSTIN pin protection[1]



1. The R_{PU} pull-up equivalent resistor is based on a resistive transistor.
2. The reset network protects the device against parasitic resets.
3. The user must ensure that the level on the NRSTIN pin can go below the $V_{IL(NRSTIN)}$ max. level specified in *Table 25*. Otherwise the reset will not be taken into account internally.

Figure 20. NRSTIN R_{PU} vs. V_{DD}



Analog power supply and reference pins

The V_{DDA} and V_{SSA} pins are the analog power supply of the A/D converter cell. They act as the high and low reference voltages for the conversion.

Separation of the digital and analog power pins allow board designers to improve A/D performance. Conversion accuracy can be impacted by voltage drops and noise in the event of heavily loaded or badly decoupled power supply lines (see*: General PCB design guidelines*).

General PCB design guidelines

To obtain best results, some general design and layout rules should be followed when designing the application PCB to shield the noise-sensitive, analog physical interface from noise-generating CMOS logic signals.

- Use separate digital and analog planes. The analog ground plane should be connected to the digital ground plane via a single point on the PCB.
- Filter power to the analog power planes. It is recommended to connect capacitors, with good high frequency characteristics, between the power and ground lines, placing 0.1 µF and optionally, if needed 10 pF capacitors as close as possible to the STR7 power supply pins and a 1 to 10 µF capacitor close to the power source (see *Figure 23*).
- The analog and digital power supplies should be connected in a star network. Do not use a resistor, as V_{DDA} is used as a reference voltage by the A/D converter and any resistance would cause a voltage drop and a loss of accuracy.
- Properly place components and route the signal traces on the PCB to shield the analog inputs. Analog signals paths should run over the analog ground plane and be as short as possible. Isolate analog signals from digital signals that may switch while the analog inputs are being sampled by the A/D converter. Do not toggle digital outputs near the A/D input being converted.

Software filtering of spurious conversion results

For EMC performance reasons, it is recommended to filter A/D conversion outliers using software filtering techniques.

Figure 23. Power supply filtering

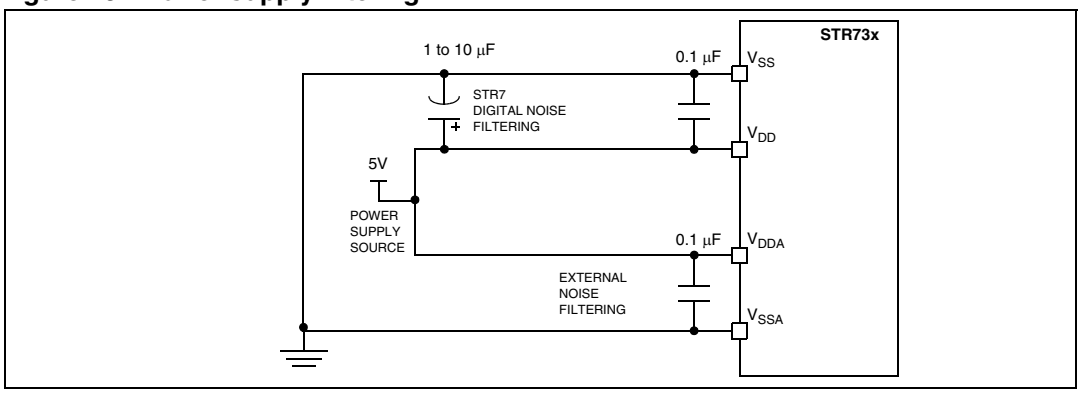
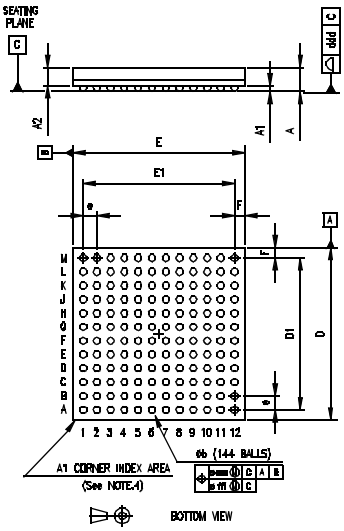


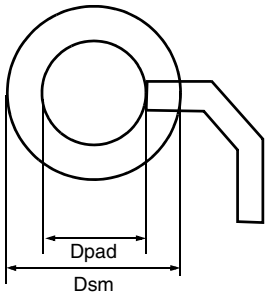
Figure 26. 144-ball low profile fine pitch ball grid array package



Dim.	mm			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	1.21		1.70	0.0476		0.0669
A1	0.21			0.0083		
A2		1.085			0.0427	
b	0.35	0.40	0.45	0.0138	0.0157	0.0177
D	9.85	10.00	10.15	0.3878	0.3937	0.3996
D1		8.80			0.3465	
E	9.85	10.00	10.15	0.3878	0.3937	0.3996
E1		8.80			0.3465	
e		0.80			0.0315	
F		0.60			0.0236	
ddd			0.10			0.0039
eee			0.15			0.0059
fff			0.08			0.0031
	Number of Pins					
N	144					

[1] Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 27. Recommended PCB design rules (0.80/0.75mm pitch BGA)



Dpad	0.37 mm
Dsm	0.52 mm typ. (depends on solder mask registration tolerance
Solder paste	0.37 mm aperture diameter
– Non solder mask defined pads are recommended – 4 to 6 mils screen print	